Abstracts

A new simplified and reliable HEMT modelling approach using pinched cold FET S-parameters

W.N. Mwema and G. Kompa. "A new simplified and reliable HEMT modelling approach using pinched cold FET S-parameters." 2000 MTT-S International Microwave Symposium Digest 00.3 (2000 Vol. III [MWSYM]): 1393-1396.

An automatic technique for determining starting values for the parasitic elements of a distributed 18 element FET directly from pinched cold FET S-parameters is described. Optimization results using this technique are presented and show that the starting vector is very close to the solution. The approach is discussed on the basis of synthesized and measured S-parameter data.

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